WNSC2D401200CW

Silicon Carbide Diode

Rev.01 - 13 August 2021 Product data sheet

1. General description

Dual Silicon Carbide Schottky diode in a 3-lead TO247 plastic package, designed for high frequency switched-mode power supplies.

2. Features and benefits

- Extremely fast reverse recovery time
- Low figure of merit (Q_C*V_F)
- Highly stable switching performance
- Superior in efficiency to Silicon Diode alternatives
- Reduced losses in associated MOSFET
- Reduced EMI
- Reduced cooling requirements
- RoHS compliant

3. Applications

- Power factor correction
- Telecom / Server SMPS
- UPS
- PV inverter
- PC Silverbox
- LED / OLED TV
- Motor Drives

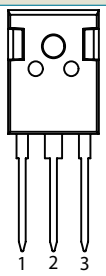
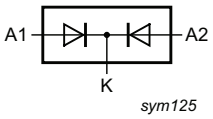
4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Values			Unit
Absolute maximum rating						
V_{RRM}	repetitive peak reverse voltage		1200			V
$I_{O(AV)}$	limiting average forward current	δ = 0.5 ; square-wave pulse; T_{mb} ≤ 105 °C; both diodes conducting; Fig. 1; Fig. 2; Fig. 3	40			A
T_j	junction temperature		175			°C
Symbol	**Parameter**	**Conditions**		**Min**	**Typ**	**Max**	**Unit**
Static characteristics							
V_F	forward voltage	I_F = 20 A; T_j = 25 °C; per diode; Fig. 5		-	1.5	1.8	V
		I_F = 20 A; T_j = 150 °C; per diode; Fig. 5		-	2.1	2.5	V
		I_F = 20 A; T_j = 175 °C; per diode; Fig. 5		-	2.25	2.8	V
Dynamic characteristics							
Q_r	recovered charge	I_F = 20 A; dI_F/dt = 500 A/µs; V_R = 400 V; T_j = 25 °C; per diode; Fig. 7		-	39	-	nC

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	A1	anode		
2	K	cathode		
3	A2	anode		
mb	mb	mounting base; connected to cathode		

6. Ordering information

Table 3. Ordering information

Type number	Package name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WNSC2D401200CW	TO247	WNSC2D401200CWQ	Tube	30	SOT429	25-Mar-2013

7. Marking

Table 4. Marking codes

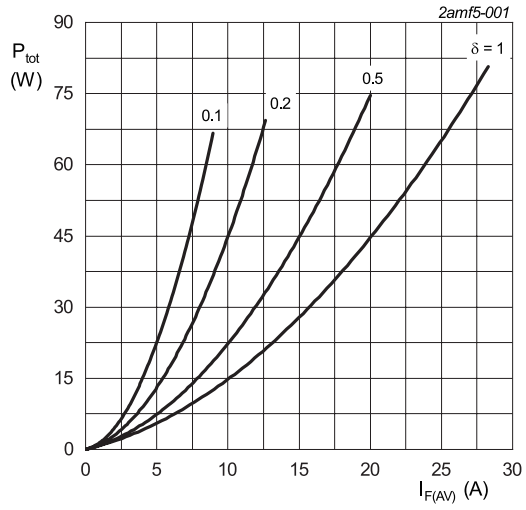
Type number	Marking codes
WNSC2D401200CW	WNSC2D 401200CW

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Values	Unit
V_{RRM}	repetitive peak reverse voltage		1200	V
V_{RWM}	crest working reverse voltage		1200	V
V_R	reverse voltage	DC	1200	V
$I_{O(AV)}$	limiting average forward current	δ = 0.5; square-wave pulse; $T_{mb} \leq 105$ °C; both diodes conducting; Fig. 1; Fig. 2; Fig. 3	40	A
I_{FRM}	repetitive peak forward current	δ = 0.5; t_p = 25 µs; $T_{mb} \leq 103$ °C; square-wave pulse; per diode	40	A
I_{FSM}	non-repetitive peak forward current	t_p = 10 ms; $T_{j(init)}$ = 25 °C; sine-wave pulse; per diode	125	A
		t_p = 10 µs; $T_{j(init)}$ = 25 °C; square-wave pulse; per diode	1150	A
I^2t	I^2t for fusing	sine-wave pulse; $T_{j(init)}$ = 25 °C; t_p = 10 ms	78	A^2s
T_{stg}	storage temperature		-55 to 175	°C
T_j	junction temperature		175	°C



$I_{F(AV)} = I_{F(RMS)} \times \sqrt{\delta}$

V_o = 0.728 V; R_s = 0.0751 Ω

Fig. 1. Forward power dissipation as a function of average forward current; square waveform; maximum values; per diode

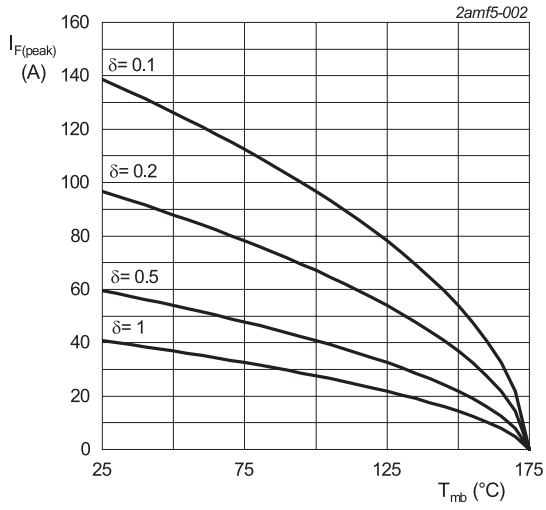


Fig. 2. Current derating as a function of mounting base temperature; per diode

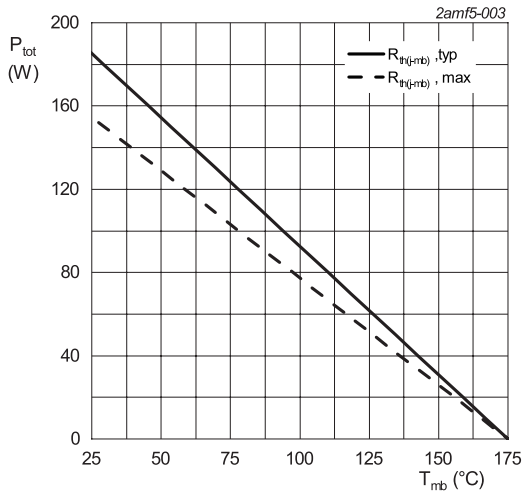


Fig. 3. Total power dissipation as a function of mounting base temperature; per diode

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	per diode; Fig. 4		-	0.81	0.97	K/W
		both diodes conducting		-	-	0.47	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient free air	in free air		-	40	-	K/W

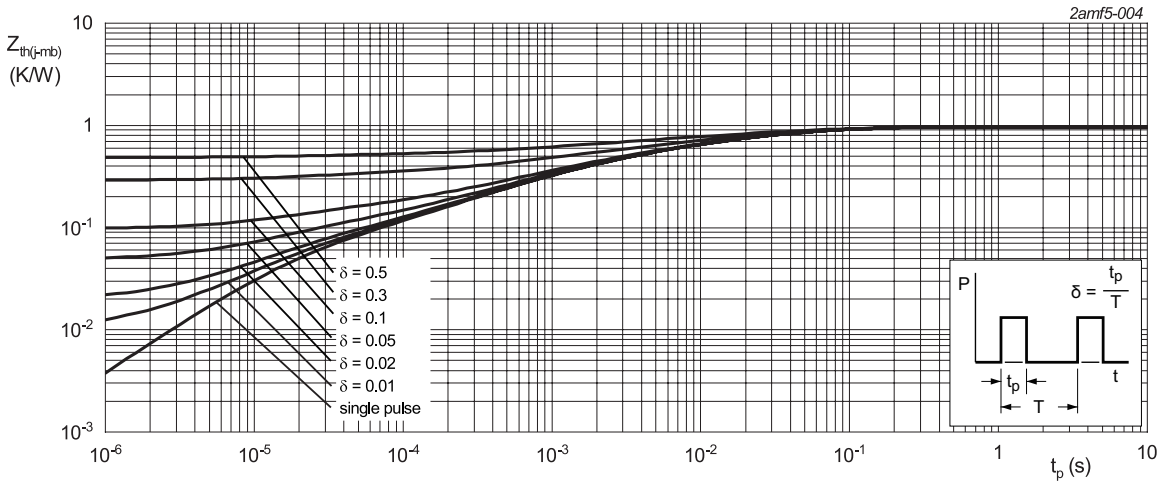
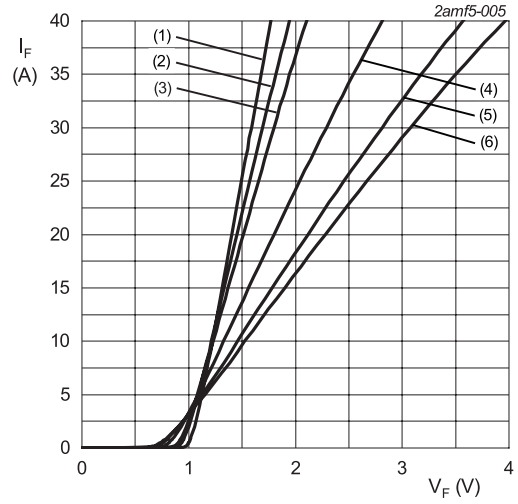


Fig. 4. Transient thermal impedance from junction to mounting base as a function of pulse duration

10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
Static characteristics							
V_F	forward current	I_F = 20 A; T_j = 25 °C; per diode; Fig. 5		-	1.5	1.8	V
		I_F = 20 A; T_j = 150 °C; per diode; Fig. 5		-	2.1	2.5	V
		I_F = 20 A; T_j = 175 °C; per diode; Fig. 5		-	2.25	2.8	V
I_R	reverse current	V_R = 1200 V; T_j = 25 °C; per diode; Fig. 6		-	8	200	µA
		V_R = 1200 V; T_j = 175 °C; per diode; Fig. 6		-	90		µA
Dynamic characteristics							
Q_r	recovered charge	I_F = 20 A; V_R = 400 V; dI_F/dt = 500 A/µs; T_j = 25 °C; per diode; Fig. 7		-	39	-	nC
C_d	diode capacitance	f = 1 MHz; V_R = 1 V; T_j = 25 °C		-	845	-	pF
		f = 1 MHz; V_R = 400 V; T_j = 25 °C		-	79	-	pF
		f = 1 MHz; V_R = 800 V; T_j = 25 °C		-	58	-	pF
E_{as}	non-repetitive avalanche energy	I_R = 5.3 A; L = 10 mH; $T_{j(init)}$ = 25 °C; per diode		140	-	-	mJ



V_o = 0.728 V; R_s = 0.0751 Ω
(1) T_j = -55 °C; typical values
(2) T_j = 0 °C; typical values
(3) T_j = 25 °C; typical values
(4) T_j = 100 °C; typical values
(5) T_j = 150 °C; typical values
(6) T_j = 175 °C; typical values

Fig. 5. Forward current as a function of forward voltage; typical values; per diode

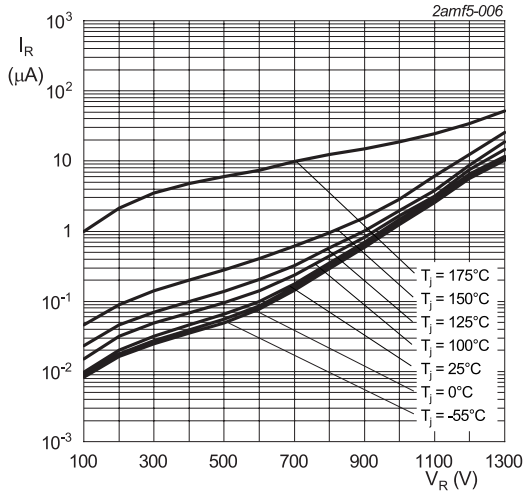


Fig. 6. Reverse leakage current as a function of reverse voltage; typical value; per diode

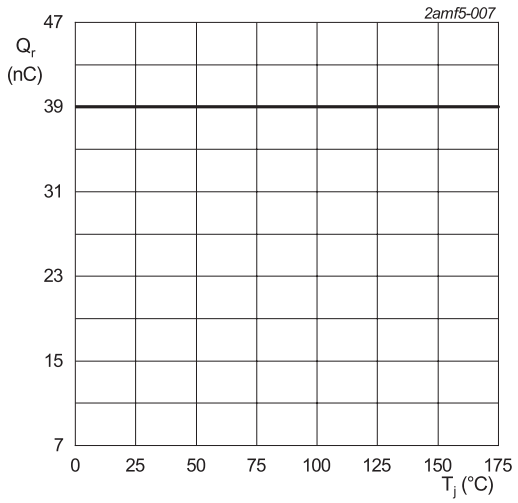
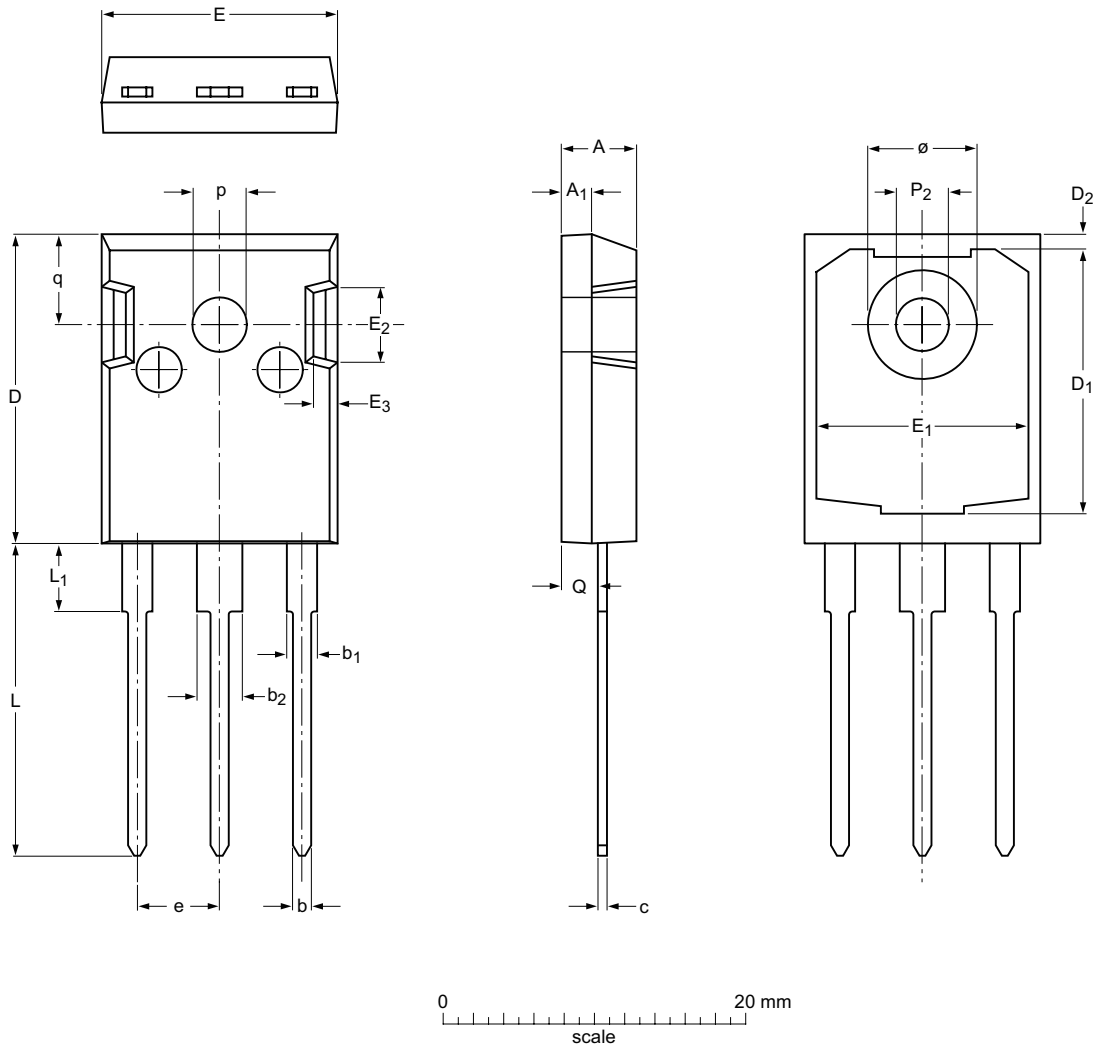


Fig. 7. Recovered charge as a function of junction temperature; per diode

11. Package outline

Plastic single-ended through-hole package; heatsink mounted; 1 mounting hole; 3-lead TO-247 **SOT429**



Dimensions (mm are the original dimensions)

Unit[1]		A	A_1	b	b_1	b_2	c	D	D_1	D_2	E	E_1	E_2	E_3	e[1]	L	L_1	P_2	p	Q	q	ø
mm	max	5.20	2.10	1.40	2.20	3.20	0.70	20.6	17.68	1.20	15.75	14.22	5.20	1.80		20.90	4.75	3.60	3.70	2.60	6.18	7.30
	nom														5.45							
	min	4.70	1.90	1.00	1.80	2.80	0.50	20.3	17.28	0.80	15.45	13.82	4.80	1.40		20.40	4.25	3.40	3.50	2.20	5.78	7.10

Note
1. Basic spacing between centers.

sot429_po

Outline version	References				European projection	Issue date
	IEC	JEDEC	JEITA			
SOT429		TO-247				~~04-09-14~~ 13-03-25

12. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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[2] The term 'short data sheet' is explained in section "Definitions".
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13. Contents

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